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Standard Guide for Minimizing Unwanted Electron Beam Effects in Auger Electron Spectroscopy¹

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Note - Changes were made throughout and the year date changed on July 25, 2005.

1. Scope

- 1.1 This guide outlines the origins and manifestations of unwanted electron beam effects in Auger electron spectroscopy (AES).
- 1.2 Some general guidelines are provided concerning the electron beam parameters which are most likely to produce these effects and suggestions are offered on how to minimize them.
- 1.3 General classes of materials are identified which are most likely to exhibit unwanted electron beam effects. In addition, a tabulation of some specific materials which have been observed to undergo electron damage effects is provided.
 - 1.4 A simple method is outlined for establishing the existence and extent of these effects during routine AES analysis.

1.5

- 1.5 The values stated in SI units are to be regarded as standard. No other units of measurement are included in this standard.
- 1.6 This standard does not purport to address all of the safety concerns, if any, associated with its use. It is the responsibility of the user of this standard to establish appropriate safety and health practices and determine the applicability of regulatory limitations prior to use.

2. Referenced Documents

2.1 ASTM Standards:²

E673 Terminology Relating to Surface Analysis
E996 Practice for Reporting Data in Auger Electron Spectroscopy and X-ray Photoelectron Spectroscopy

3. Terminology

3.1 See Terminology E673 for terms used in Auger electron spectroscopy.

Note 1—Electron beam effects and their consequences are widely referred to in the literature using any one or more of the following terms: electron beam damage, sample damage, specimen damage, beam effects, electron beam induced processes, and electron irradiation effects.

4. Significance and Use

- 4.1 When electron beam excitation is used in AES, the incident electron beam can interact with the specimen material causing physical and chemical changes. In general, these effects are a hindrance to AES analysis because they cause localized specimen modification (1, 2, 3, 41-4).
- 4.2 With specimens that have poor electrical conductivity the electron beam can stimulate the development of localized charge on the specimen surface. This effect is a hindrance to AES analysis because the potentials associated with the charge can either adversely affect the integrity of Auger data or make Auger data collection difficult (5, 6).

5. Origins of Electron Beam Effects

- 5.1 Electron beam effects in AES may originate from one or more distinct processes.
- 5.1.1 Charge accumulation (57) (see Chapter 9) in materials with poor electrical conductivity leading to potentials that cause distortion of Auger data or make AES data collection difficult by virtue of:

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² For referenced ASTM standards, visit the ASTM website, www.astm.org, or contact ASTM Customer Service at service@astm.org. For *Annual Book of ASTM Standards* volume information, refer to the standard's Document Summary page on the ASTM website.

³ The boldface numbers in parentheses refer to the references listed at the end of this standard.



- 5.1.1.1 Auger peak shift on energy seale.scale,
- 5.1.1.2 Auger peak shape and size distortion, and
- 5.1.1.3 Auger signal strength instability.
- 5.1.2 Electronic excitation of surface, subsurface, and bulk atoms and molecules leading to specimen changes (6-88-10) which include:
 - 5.1.2.1Dissociation.
 - 5.1.2.1 Dissociation,
 - 5.1.2.2 Electron stimulated desorption (ESD) (911).
 - 5.1.2.3 Electron stimulated adsorption (ESA) (1012)-,
 - 5.1.2.4 Polymerization (1113, 1214).-,
 - 5.1.2.5 Carburization (13-1515-17).-,
 - 5.1.2.6 Oxidation (1618, 1719).-,
 - 5.1.2.7 Reduction (**1820**)...,
 - 5.1.2.8 Decomposition (1921, 2022).
 - 5.1.2.9Erosion.,
 - 5.1.2.9 Erosion, and
 - 5.1.2.10 Diffusion.
- 5.1.3 Charge accumulation in materials of poor electrical conductivity leading to specimen changes which include (2123, 2224, 57) (see Chapter 8):
 - 5.1.3.1Electric field enhanced diffusion.
 - 5.1.3.1 Electric field enhanced diffusion, and
 - 5.1.3.2 Electromigration (4) (see p. 62).
 - 5.1.4 Heating which may cause:
 - 5.1.4.1 Annealing.
 - 5.1.4.2Segregation.
 - 5.1.4.3 Volatilization.
 - 5.1.4.1 Annealing,
 - 5.1.4.2 Segregation,
 - 5.1.4.3 Volatilization, and
 - 5.1.4.4 Chemical reaction.

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6. Practical Manifestations of Electron Beam Effects

- 6.1 Electron dose dependent changes in the intensity, energy, or peak shape of one or more Auger transitions, or any combination thereof; depending upon the material, these changes may be complete within a fraction of a second or they may progress for hours. dards iteh alcatalog/standards/sist/a75bbc0b-7f6a-4ee4-800f-a14a6b556cc1/astm-e983-10
- 6.2 Discoloration of the specimen atin the proximity of the electron beam irradiated region.
 - 6.3 Physical damage to the specimen such as erosion, cracking, blistering, or densification.
 - 6.4 Pressure rises in the analytical vacuum chamber during electron irradiation.
- 6.5 Localized electric charge dependent changes in the intensity, energy, or peak shape of all Auger transitions, or any combination thereof. These changes may be stable but often are erratic resulting in unstable AES signals which may preclude AES data collection.

7. Electron Beam Parameters

- 7.1 Electron Dose and Current Density:
- 7.1.1 Electron dose and current density were previously defined using units of C/cm² and mA/cm², respectively. These units are not consistent with the SI system. To keep from changing the magnitude of the numbers appearing in the literature (from which Table 1 is adapted), the multipliers of the terms are being changed. A dose of C/cm² is equivalent to 10⁴C/m², while 1mA/cm² is equivalent to 10A/m².
- 7.1.2 Specimen material modification can often be related to the electron dose (D); that is, the number of electrons incident on a unit area of the specimen, expressed in coulombs per square centimeter (C/cm^2) (1).
- 7.1.3 A number of materials, (for example, see Table 1), exhibit dose-dependent effects when the electron dose exceeds a material specific critical dose₂ D_c . The magnitude of the critical dose corresponds to the onset of detectable damage and the values may be subject to future revision. The material specific <u>critical</u> dose, D_c , may be as low as $\frac{10A}{m1} \frac{C}{m^2}$.
- 7.1.4 In practice, the electron dose is directly dependent upon the electron beam current density, J_B , (A/m^2) , the time of electron irradiation in seconds, t (s); and the angle of incidence, Θ , of the beam on the sample. That is, D_C (C/m^2) = J_B (A/m^2)·t (s)·cos Θ . Putting the electron beam current density into commonly used condition, $10A/m^{(s)\cdot\cos\Theta}$. Using a typical electron beam current density, $10A/m^2$ would be equivalent to using 10^{-8} A incident beam current into a 33 µm electron beam diameter at normal incidence.
- 7.1.5 The electron beam-induced heating of a given material of poor thermal conductivity and the accumulation of charge on a material of poor electrical conductivity are dependent upon the electron beam current density.